

1. Global joint venture starts operations as WeEn Semiconductors

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WeEn Semiconductors



Product data sheet

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT223 (SC-73) surface-mountable plastic package intended for applications requiring enhanced immunity to noise and direct interfacing to logic level ICs and low power gate drivers.

2. Features and benefits

- Direct interfacing to logic level ICs
- Enhanced current surge capability
- Enhanced noise immunity
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate in four quadrants
- Surface-mountable package
- Triggering in all four quadrants

3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	-	12.5	Α
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 105 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	-	1	Α
Static characte	eristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 9$	0.4	-	10	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 9}}{}$	0.4	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 9$	0.4	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 9$	0.4	-	10	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2—T1
2	T2	main terminal 2		Sym051
3	G	gate		y
4	T2	main terminal 2	☐1 ☐2 ☐3 SC-73 (SOT223)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
Z0109NN0	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

7. Marking

Table 4. Marking codes

Type number	Marking code
Z0109NN0	109NN0

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 105 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	1	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	12.5	A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	13.8	А
I ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.78	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2+ G+	-	50	A/µs
		I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2+ G-	-	50	A/µs
		I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2- G-	-	50	A/µs
		I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2- G+	-	20	A/µs
I _{GM}	peak gate current		-	1	Α
P_GM	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

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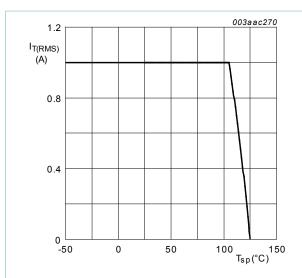
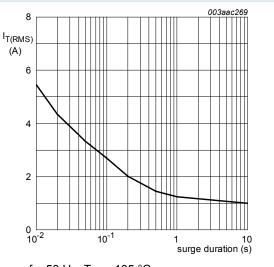
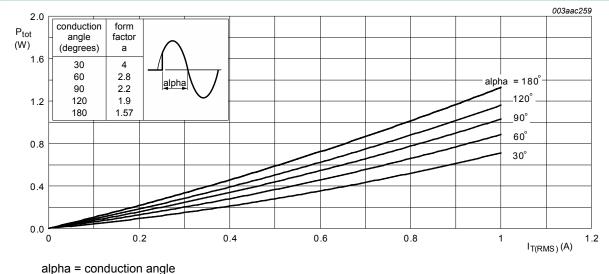


Fig. 1. RMS on-state current as a function of solder point temperature; maximum values



 $f = 50 \text{ Hz}; T_{sp} = 105 \,^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values



a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

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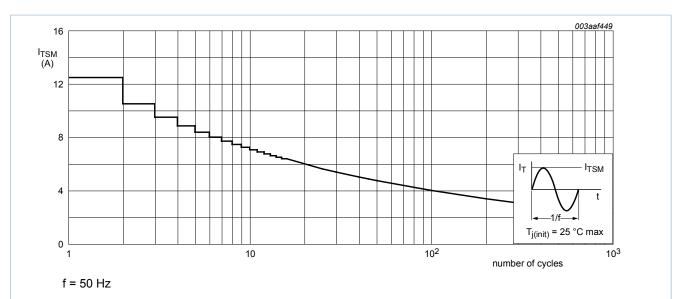


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

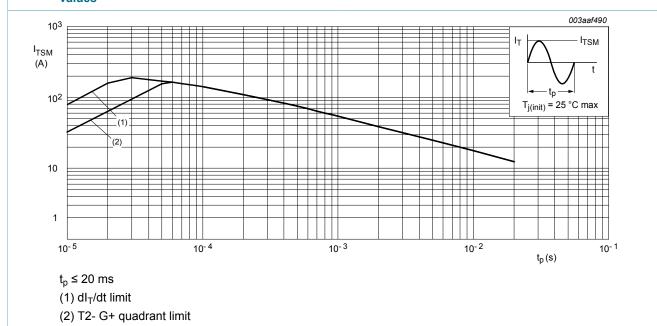


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

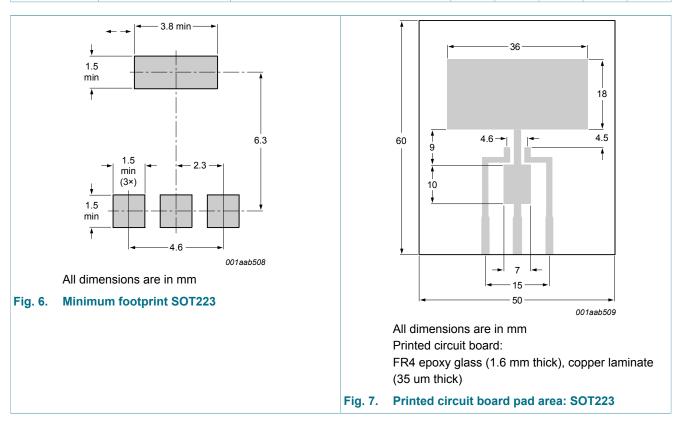
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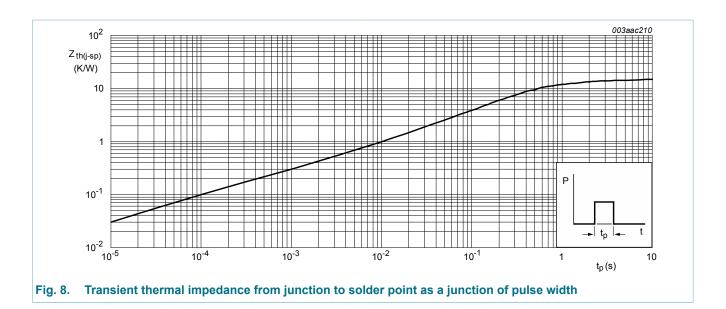
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	full cycle; Fig. 8	-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air; printed-circuit board mounted: minimum footprint; full cycle; Fig. 6	-	156	-	K/W
		in free air; printed-circuit board mounted: pad area; full cycle; Fig. 7	-	70	-	K/W



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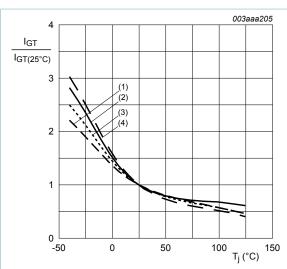
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
l _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 9$	0.4	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 9$	0.4	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 9}}$	0.4	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 9}$	0.4	-	10	mA
L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G-;$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 10}}$	-	-	15	mA
Н	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	-	10	mA
/ _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.3	1.6	V
/ _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 13	-	-	1	V
		$V_D = 800 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 °C;$ Fig. 13	0.2	-	-	V
D	off-state current	V _D = 800 V; T _j = 125 °C	-	-	0.5	mA
Dynamic ch	naracteristics		1	-	-	
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 14	120	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 110 \text{ °C}; \text{ dI}_{com}/$ dt = 0.44 A/ms; gate open circuit	2	-	-	V/µs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 9. Normalized gate trigger current as a function of junction temperature

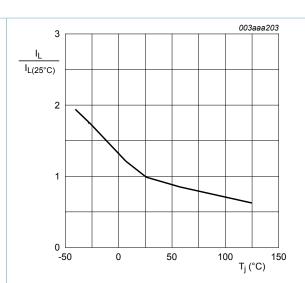


Fig. 10. Normalized latching current as a function of junction temperature

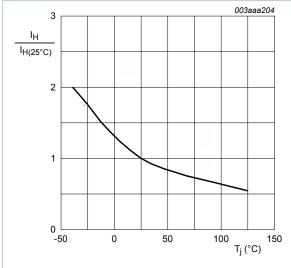
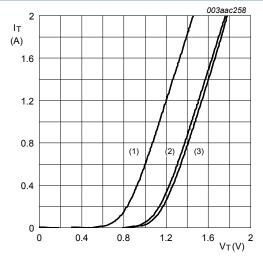


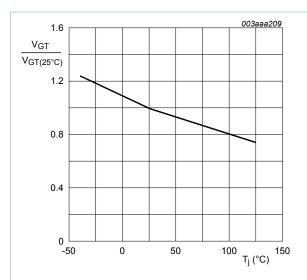
Fig. 11. Normalized holding current as a function of junction temperature



- $V_0 = 1.13 \text{ V}$
- R_s = 0.31 Ω
- (1) T_i = 125 °C; typical values
- (2) T_i = 125 °C; maximum values
- (3) T_i = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

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junction temperature

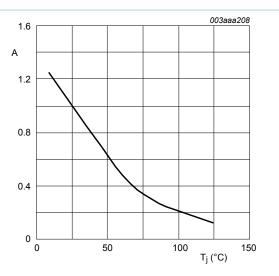
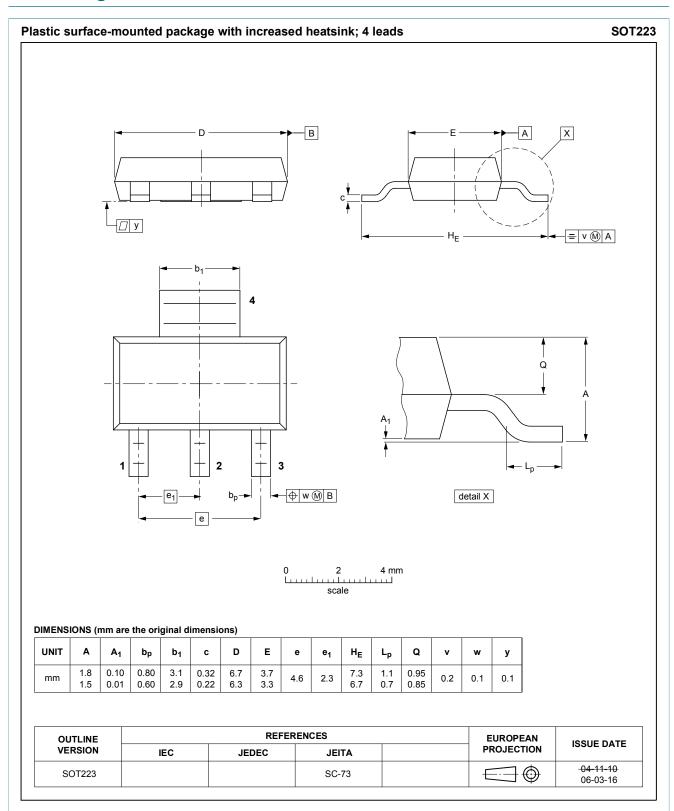


Fig. 13. Normalized gate trigger voltage as a function of Fig. 14. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

$$A = \frac{d\mathrm{V}_{D(Tj\,^{\circ}\,C)}\,/\,\,dt}{d\mathrm{V}_{D(25\,^{\circ}\,C)}/\,\,dt}$$

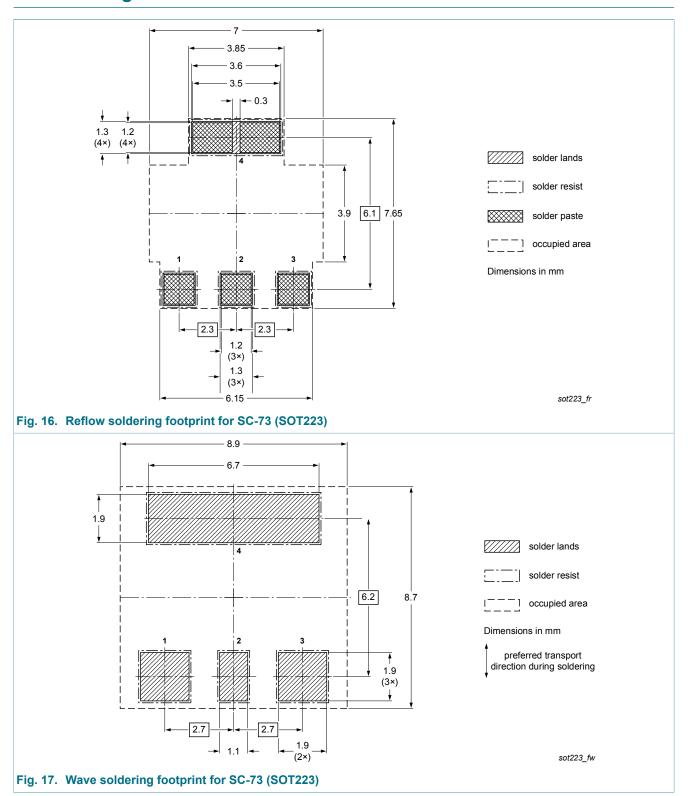
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11. Package outline



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12. Soldering



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13. Legal information

13.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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